

ABSTRACT

Damages in the semiconductor layers at the chip separating surfaces are suppressed in a semiconductor laser employing a GaN-based semiconductor substrate made of GaN and AlGa_N. Laminated layers including a n-type clad layer (502) made of AlGa_N and a multi-quantum well (MQW) layer (504) serving to be an active layer is formed on an independent GaN substrate (501). The side surfaces of the laminated layers along the direction of the resonator are inclined in such a direction that the resonator width is decreased from the independent GaN substrate (501) to the laminated layers.